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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
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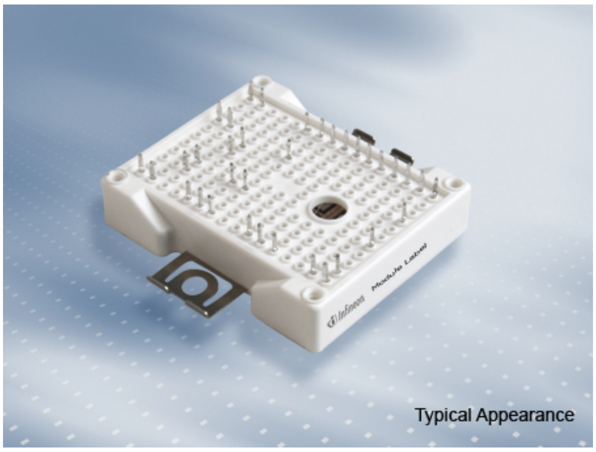
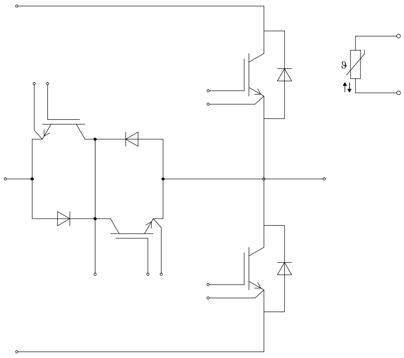
F3L225R07W2H3P_B63

EasyPACK™ Modul mit aktiver "Neutral Point Clamp 2" Topologie und PressFIT / NTC / TIM
EasyPACK™ module with active "Neutral Point Clamp 2" topology and PressFIT / NTC / TIM





V_{CES} = 650V
$I_{C\ nom}$ = 125A / I_{CRM} = 250A

Typische Anwendungen
- 3-Level-Applikationen
- Motorantriebe
- Solar Anwendungen
- USV-Systeme

Typical Applications
- 3-level-applications
- Motor drives
- Solar applications
- UPS systems

Elektrische Eigenschaften
- High Speed IGBT H3
- $T_{vj\ op}$ = 150°C

Electrical Features
- High speed IGBT H3
- $T_{vj\ op}$ = 150°C

Mechanische Eigenschaften
- 2,5 kV AC 1min Isolationsfestigkeit
- Integrierter NTC Temperatur Sensor
- PressFIT Verbindungstechnik
- RoHS konform
- Thermisches Interface Material bereits aufgetragen

Mechanical Features
- 2.5 kV AC 1min insulation
- Integrated NTC temperature sensor
- PressFIT contact technology
- RoHS compliant
- Pre-applied Thermal Interface Material

Module Label Code

Barcode Code 128

00000123456000000000000

DMX - Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, T1 / T4 / IGBT, T1 / T4

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	650	V
Implementierter Kollektor-Strom Implemented collector current		I_{CN}	225	A
Kollektor-Dauergleichstrom Continuous DC collector current	T_H = 95°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$	125	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	t_P = 1 ms	I_{CRM}	450	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

				min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	I_C = 125 A, V_{GE} = 15 V I_C = 125 A, V_{GE} = 15 V I_C = 125 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE\,sat}$		1,40 1,45 1,45	1,65	V V V
Gate-Schwellenspannung Gate threshold voltage	I_C = 3,60 mA, V_{CE} = V_{GE}, T_{vj} = 25°C		V_{GEth}	5,05	5,80	6,45	V
Gateladung Gate charge	V_{GE} = -15 V ... +15 V		Q_G		2,40		µC
Interner Gatewiderstand Internal gate resistor	T_{vj} = 25°C		R_{Gint}		0,0		Ω
Eingangskapazität Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		14,0		nF
Rückwirkungskapazität Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{res}		0,42		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	V_{CE} = 650 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	I_C = 125 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Gon} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,on}$		0,06 0,07 0,07		µs µs µs
Anstiegszeit, induktive Last Rise time, inductive load	I_C = 125 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Gon} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0,09 0,10 0,10		µs µs µs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	I_C = 125 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Goff} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,off}$		0,06 0,07 0,07		µs µs µs
Fallzeit, induktive Last Fall time, inductive load	I_C = 125 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Goff} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0,03 0,04 0,04		µs µs µs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	I_C = 125 A, V_{CE} = 400 V, L_S = 25 nH V_{GE} = ±15 V, di/dt = 1500 A/µs (T_{vj} = 150°C) R_{Gon} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		8,50 10,0 10,5		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	I_C = 125 A, V_{CE} = 400 V, L_S = 25 nH V_{GE} = ±15 V, du/dt = 2900 V/µs (T_{vj} = 150°C) R_{Goff} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		4,40 5,20 5,80		mJ mJ mJ
Kurzschlußverhalten SC data	V_{GE} ≤ 15 V, V_{CC} = 400 V V_{CEmax} = V_{CES} $-L_{sCE}$ ·di/dt	t_P ≤ 0 µs, T_{vj} = 150°C	I_{SC}		1300		A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}			0,364	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

Diode, D2 / D3 / Diode, D2 / D3

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	650	V
Implementierter Durchlassstrom Implemented forward current		I_{FN}	100	A
Dauergleichstrom Continuous DC forward current		I_F	85	A
Periodischer Spitzenstrom Repetitive peak forward current	t_P = 1 ms	I_{FRM}	200	A
Grenzlastintegral I²t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I^2t	850 800	A²s A²s

Charakteristische Werte / Characteristic Values

				min.	typ.	max.	
Durchlassspannung Forward voltage	I_F = 85 A, V_{GE} = 0 V I_F = 85 A, V_{GE} = 0 V I_F = 85 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,55 1,50 1,45	2,00	V V V
Rückstromspitze Peak reverse recovery current	I_F = 85 A, - di_F/dt = 1300 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		37,0 52,0 57,0		A A A
Sperrverzögerungsladung Recovered charge	I_F = 85 A, - di_F/dt = 1300 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		2,50 4,80 5,60		µC µC µC
Abschaltenergie pro Puls Reverse recovery energy	I_F = 85 A, - di_F/dt = 1300 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		0,24 0,65 0,79		mJ mJ mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode valid with IFX pre-applied thermal interface material		R_{thJH}			0,935	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\ op}$	-40		150	°C

IGBT, T2 / T3 / IGBT, T2 / T3

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	650	V
Implementierter Kollektor-Strom Implemented collector current		I_{CN}	100	A
Kollektor-Dauergleichstrom Continuous DC collector current	T_H = 25°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$	85	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	t_P = 1 ms	I_{CRM}	200	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

				min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	I_C = 85 A, V_{GE} = 15 V I_C = 85 A, V_{GE} = 15 V I_C = 85 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE\,sat}$		1,35 1,50 1,55	1,75	V V V
Gate-Schwellenspannung Gate threshold voltage	I_C = 1,60 mA, V_{CE} = V_{GE}, T_{vj} = 25°C		V_{GEth}	4,95	5,80	6,45	V
Gateladung Gate charge	V_{GE} = -15 V ... +15 V		Q_G		1,00		µC
Interner Gatewiderstand Internal gate resistor	T_{vj} = 25°C		R_{Gint}		2,0		Ω
Eingangskapazität Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		6,20		nF
Rückwirkungskapazität Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{res}		0,19		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	V_{CE} = 650 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	I_C = 85 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Gon} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,on}$		0,07 0,08 0,08		µs µs µs
Anstiegszeit, induktive Last Rise time, inductive load	I_C = 85 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Gon} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0,04 0,05 0,05		µs µs µs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	I_C = 85 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Goff} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,off}$		0,35 0,40 0,40		µs µs µs
Fallzeit, induktive Last Fall time, inductive load	I_C = 85 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Goff} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0,05 0,10 0,10		µs µs µs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	I_C = 85 A, V_{CE} = 400 V, L_S = 25 nH V_{GE} = ±15 V, di/dt = 1300 A/µs (T_{vj} = 150°C) R_{Gon} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		4,80 7,10 7,60		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	I_C = 85 A, V_{CE} = 400 V, L_S = 25 nH V_{GE} = ±15 V, du/dt = 3500 V/µs (T_{vj} = 150°C) R_{Goff} = 10 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		2,50 3,80 4,20		mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq$ 15 V, V_{CC} = 400 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt	$t_P \leq$ 6 µs, T_{vj} = 150°C	I_{SC}		500		A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}			0,802	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

Diode, D1 / D4 / Diode, D1 / D4

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	650	V
Implementierter Durchlassstrom Implemented forward current		I_{FN}	225	A
Dauergleichstrom Continuous DC forward current		I_F	125	A
Periodischer Spitzenstrom Repetitive peak forward current	t_P = 1 ms	I_{FRM}	450	A
Grenzlastintegral I^2t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I^2t	3750 3500	A²s A²s

Charakteristische Werte / Characteristic Values

				min.	typ.	max.	
Durchlassspannung Forward voltage	I_F = 125 A, V_{GE} = 0 V I_F = 125 A, V_{GE} = 0 V I_F = 125 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,35 1,25 1,20	1,55	V V V
Rückstromspitze Peak reverse recovery current	I_F = 125 A, - di_F/dt = 1500 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		46,0 70,0 76,0		A A A
Sperrverzögerungsladung Recovered charge	I_F = 125 A, - di_F/dt = 1500 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		6,40 12,5 14,5		µC µC µC
Abschaltenergie pro Puls Reverse recovery energy	I_F = 125 A, - di_F/dt = 1500 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		1,30 2,90 3,30		mJ mJ mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode valid with IFX pre-applied thermal interface material		R_{thJH}			0,419	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

Modul / Module

Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}		2,5		kV
Innere Isolation Internal isolation	Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)			Al_2O_3		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal			11,5 6,3		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal			10,0 5,0		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI		> 200		
			min.	typ.	max.	
Modulstreuinduktivität Stray inductance module		L_{sCE}		15		nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T_H = 25°C, pro Schalter / per switch	$R_{CC'+EE'}$		1,25		mΩ
Lagertemperatur Storage temperature		T_{stg}	-40		125	°C
Höchstzulässige Bodenplattenbetriebstemperatur Maximum baseplate operation temperature		T_{BPmax}			125	°C
Anpresskraft für mech. Bef. pro Feder mountig force per clamp		F	40	-	80	N
Gewicht Weight		G		41		g

Der Strom im Dauerbetrieb ist auf 25A effektiv pro Anschlusspin begrenzt.
The current under continuous operation is limited to 25A rms per connector pin.
Lagerung und Transport von Modulen mit TIM => siehe AN2012-07
Storage and Shipment of modules with TIM => see AN2012-07

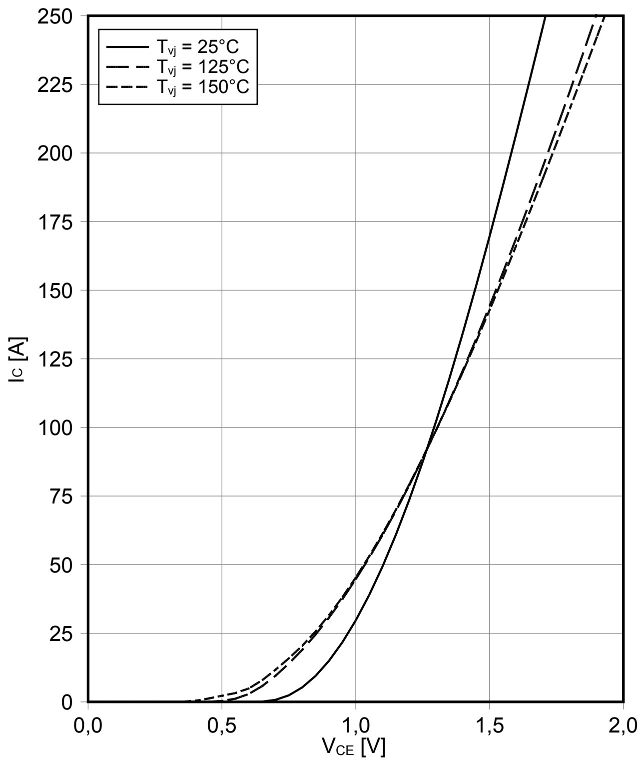
NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

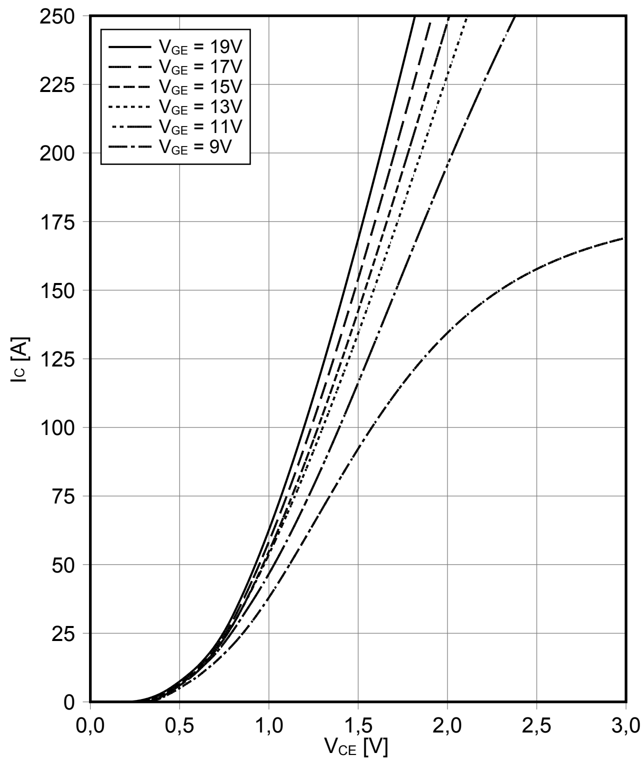
			min.	typ.	max.	
Nennwiderstand Rated resistance	T_{NTC} = 25°C	R_{25}		5,00		kΩ
Abweichung von R100 Deviation of R100	T_{NTC} = 100°C, R_{100} = 493 Ω	ΔR/R	-5		5	%
Verlustleistung Power dissipation	T_{NTC} = 25°C	P_{25}			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\ K))]$	$B_{25/50}$		3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\ K))]$	$B_{25/80}$		3411		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\ K))]$	$B_{25/100}$		3433		K

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

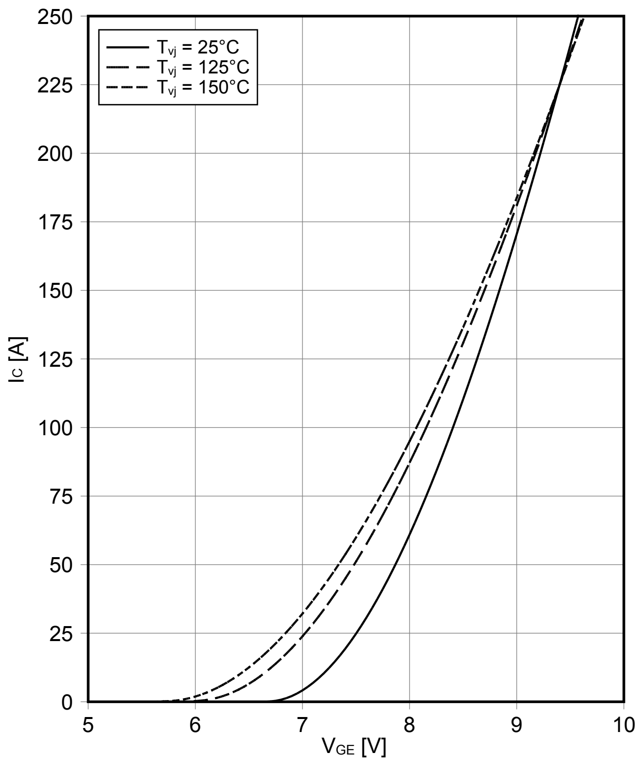
Ausgangskennlinie IGBT, T1 / T4 (typisch)
output characteristic IGBT, T1 / T4 (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V



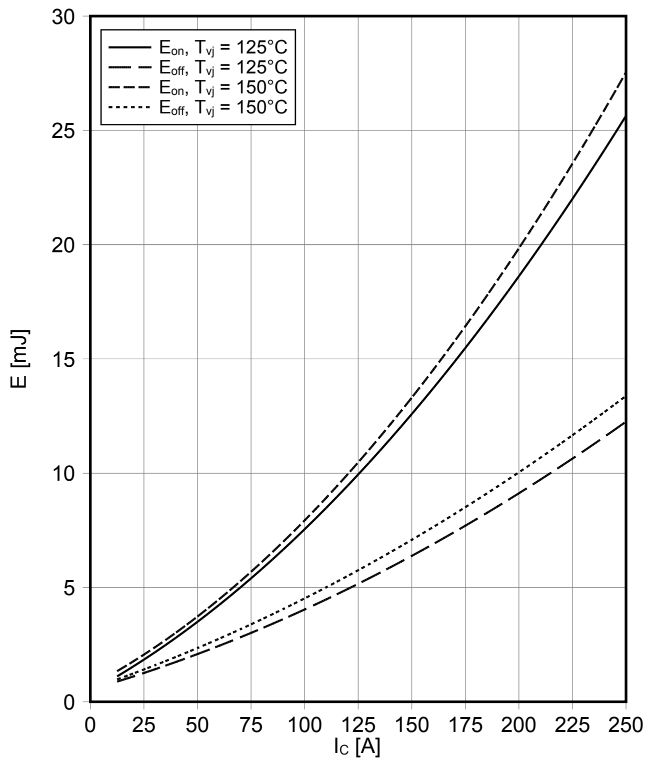
Ausgangskennlinienfeld IGBT, T1 / T4 (typisch)
output characteristic IGBT, T1 / T4 (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150$°C



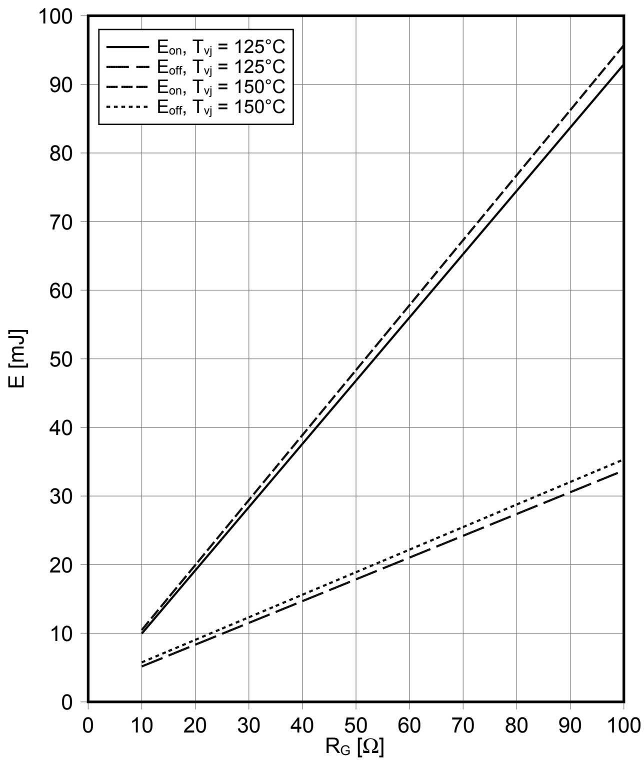
Übertragungscharakteristik IGBT, T1 / T4 (typisch)
transfer characteristic IGBT, T1 / T4 (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



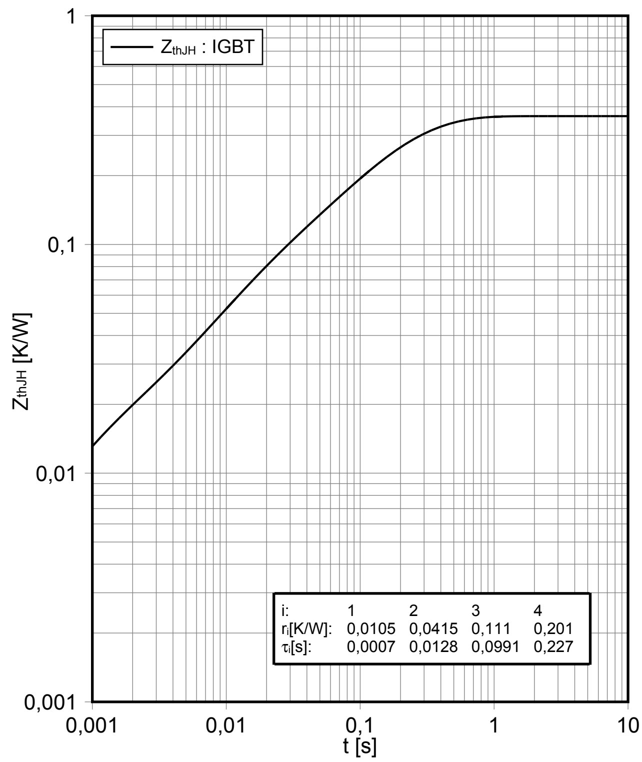
Schaltverluste IGBT, T1 / T4 (typisch)
switching losses IGBT, T1 / T4 (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$V_{GE} = \pm15$ V, $R_{Gon} = 10\ \Omega$, $R_{Goff} = 10\ \Omega$, $V_{CE} = 400$ V



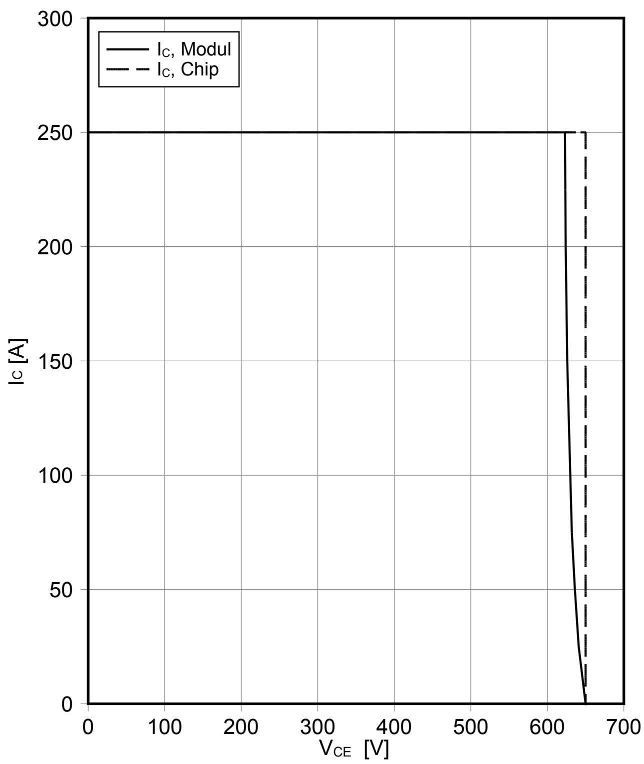
Schaltverluste IGBT, T1 / T4 (typisch)
switching losses IGBT, T1 / T4 (typical)
E_{on} = f (R_G), E_{off} = f (R_G)
V_{GE} = ±15 V, I_C = 125 A, V_{CE} = 400 V



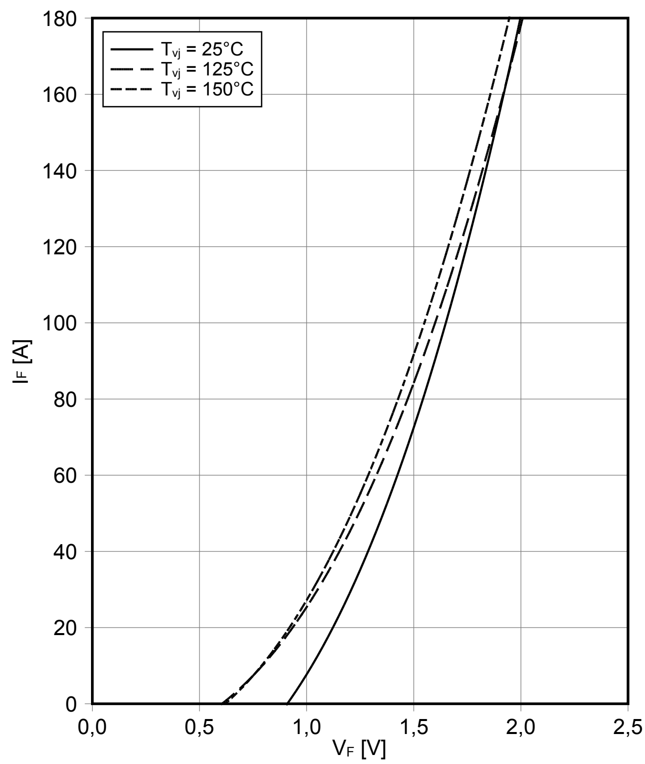
Transienter Wärmewiderstand IGBT, T1 / T4
transient thermal impedance IGBT, T1 / T4
Z_{thJH} = f (t)



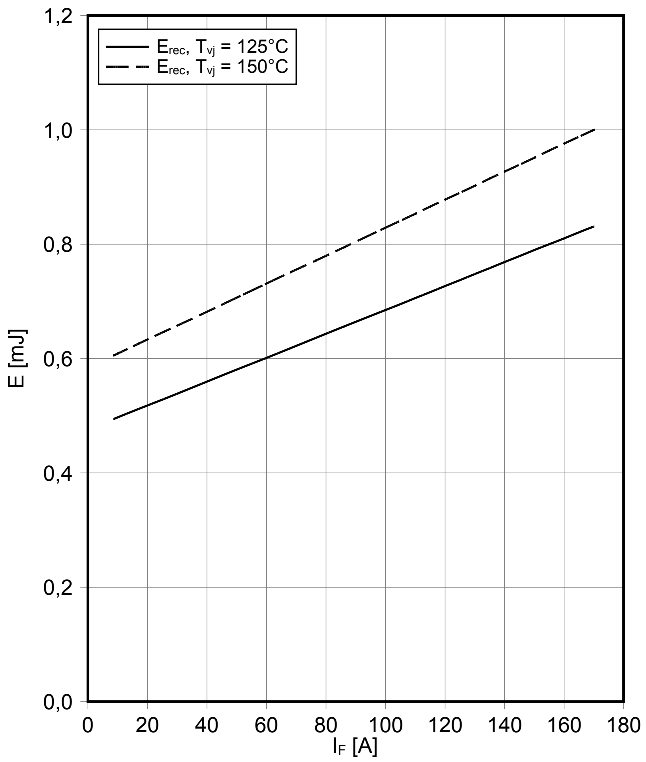
Sicherer Rückwärts-Arbeitsbereich IGBT, T1 / T4 (RBSOA)
reverse bias safe operating area IGBT, T1 / T4 (RBSOA)
I_C = f (V_{CE})
V_{GE} = ±15 V, R_{Goff} = 10 Ω, T_{vj} = 150°C



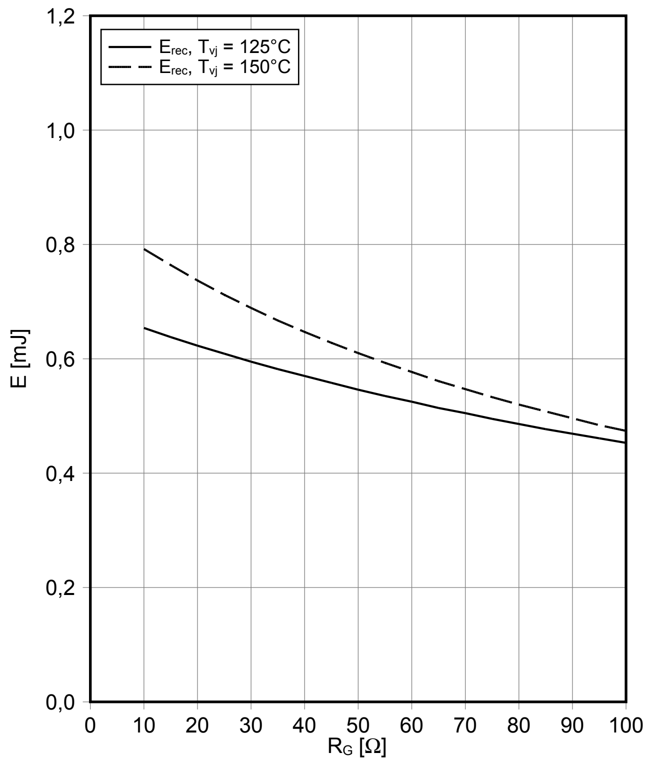
Durchlasskennlinie der Diode, D2 / D3 (typisch)
forward characteristic of Diode, D2 / D3 (typical)
I_F = f (V_F)



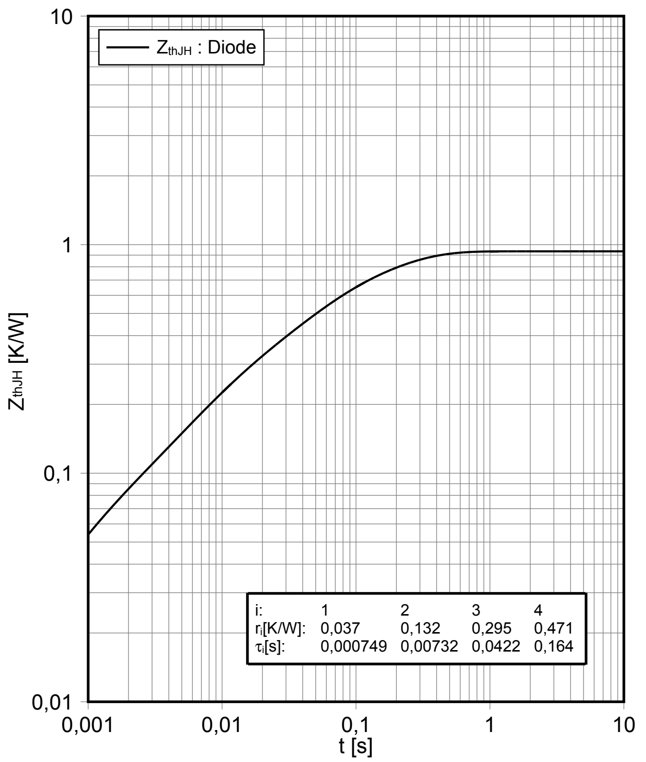
Schaltverluste Diode, D2 / D3 (typisch)
switching losses Diode, D2 / D3 (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 10\ \Omega$, $V_{CE} = 400$ V



Schaltverluste Diode, D2 / D3 (typisch)
switching losses Diode, D2 / D3 (typical)
$E_{rec} = f(R_G)$
$I_F = 85$ A, $V_{CE} = 400$ V

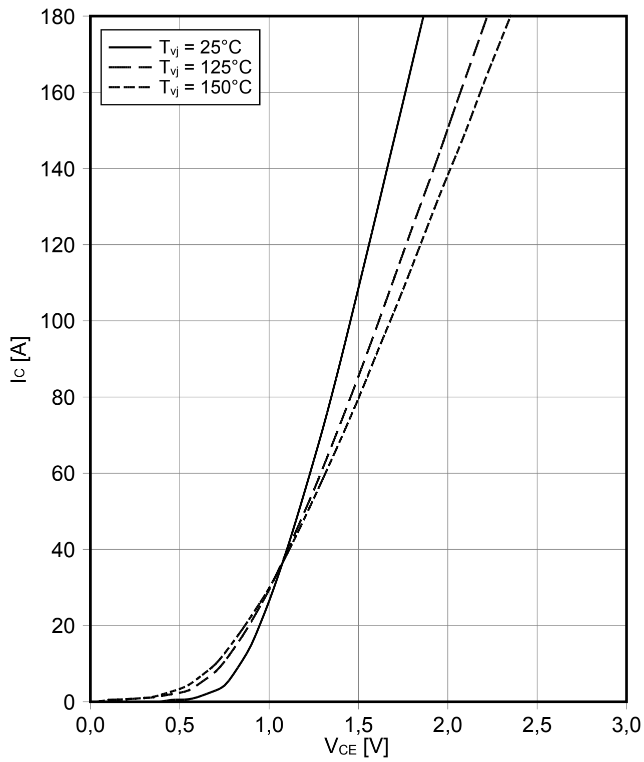


Transienter Wärmewiderstand Diode, D2 / D3
transient thermal impedance Diode, D2 / D3
$Z_{thJH} = f(t)$

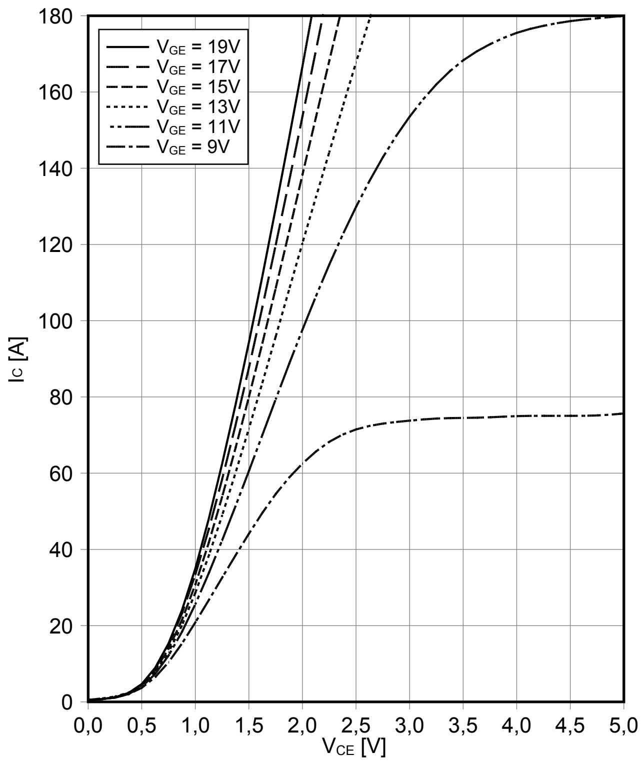


i:	1	2	3	4
r_i[K/W]:	0,037	0,132	0,295	0,471
τ_i[s]:	0,000749	0,00732	0,0422	0,164

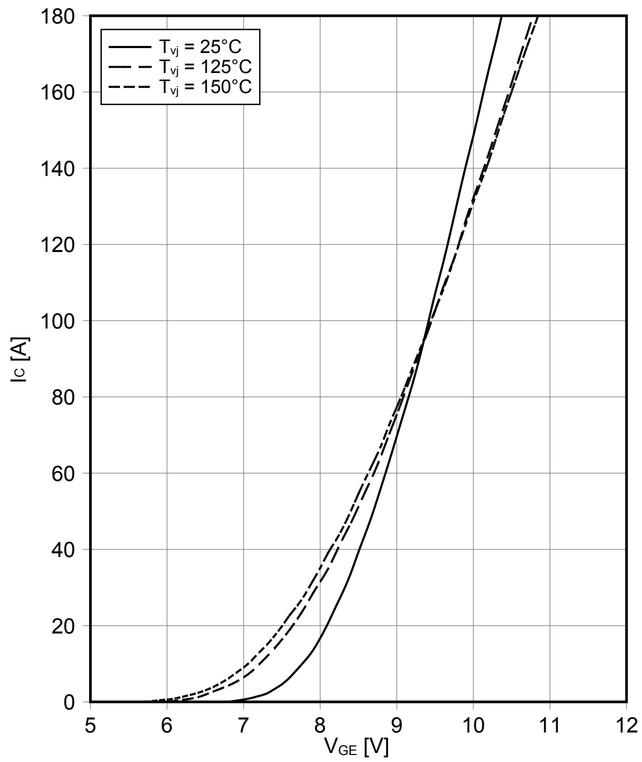
Ausgangskennlinie IGBT, T2 / T3 (typisch)
output characteristic IGBT, T2 / T3 (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V



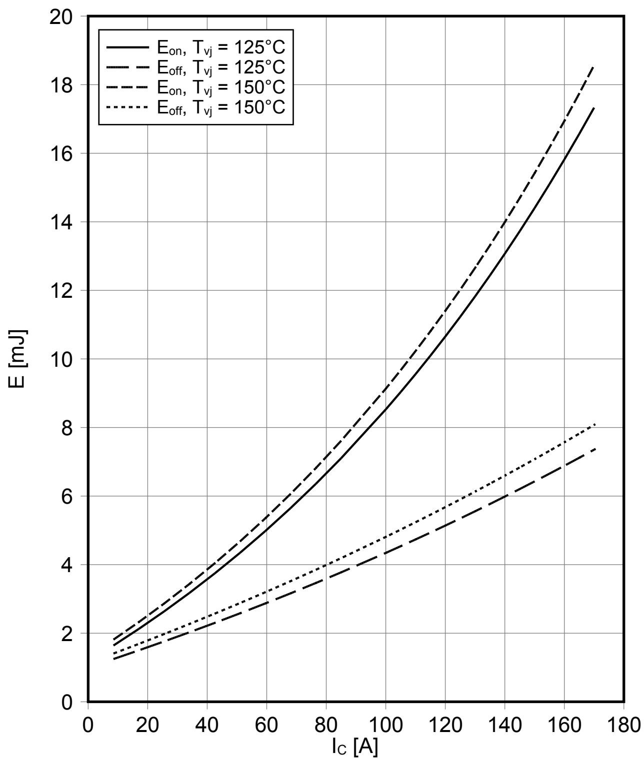
Ausgangskennlinienfeld IGBT, T2 / T3 (typisch)
output characteristic IGBT, T2 / T3 (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150°C$



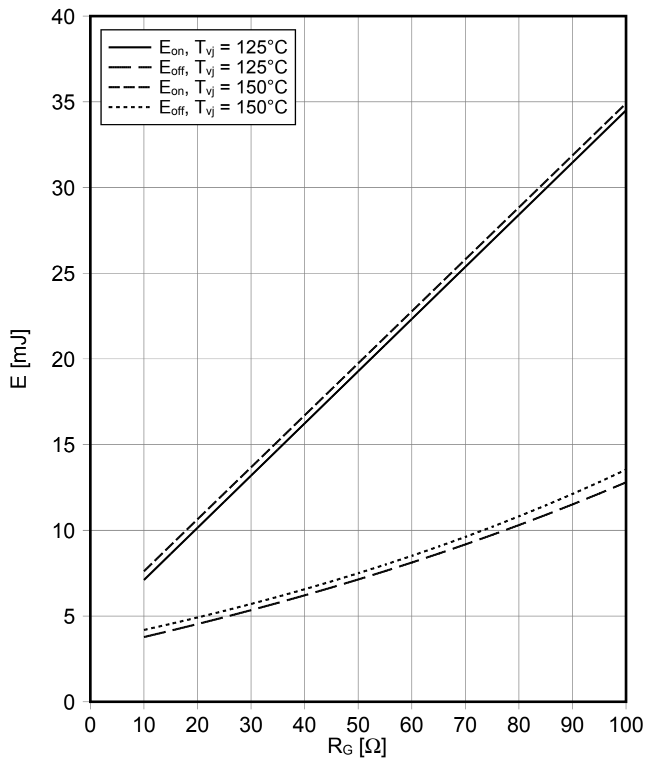
Übertragungscharakteristik IGBT, T2 / T3 (typisch)
transfer characteristic IGBT, T2 / T3 (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20\ V$



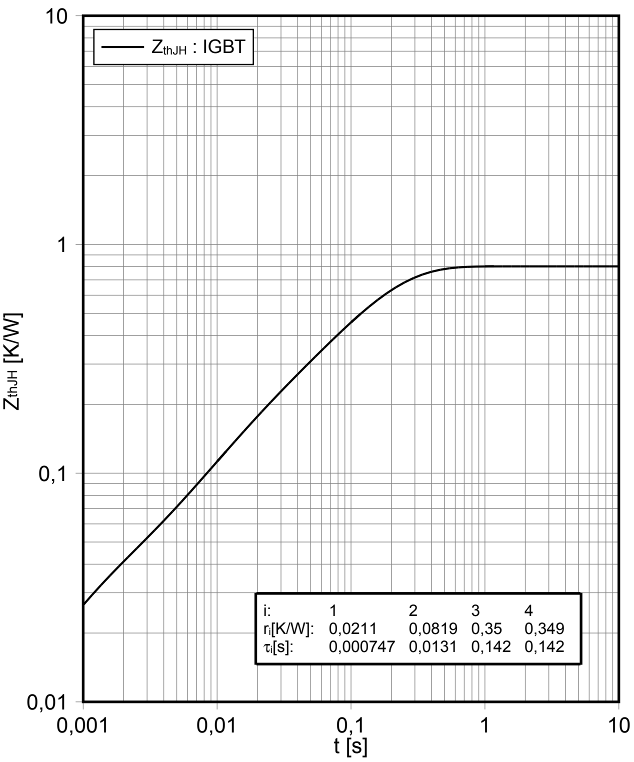
Schaltverluste IGBT, T2 / T3 (typisch)
switching losses IGBT, T2 / T3 (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$V_{GE} = \pm15\ V$, $R_{Gon} = 10\ \Omega$, $R_{Goff} = 10\ \Omega$, $V_{CE} = 400\ V$



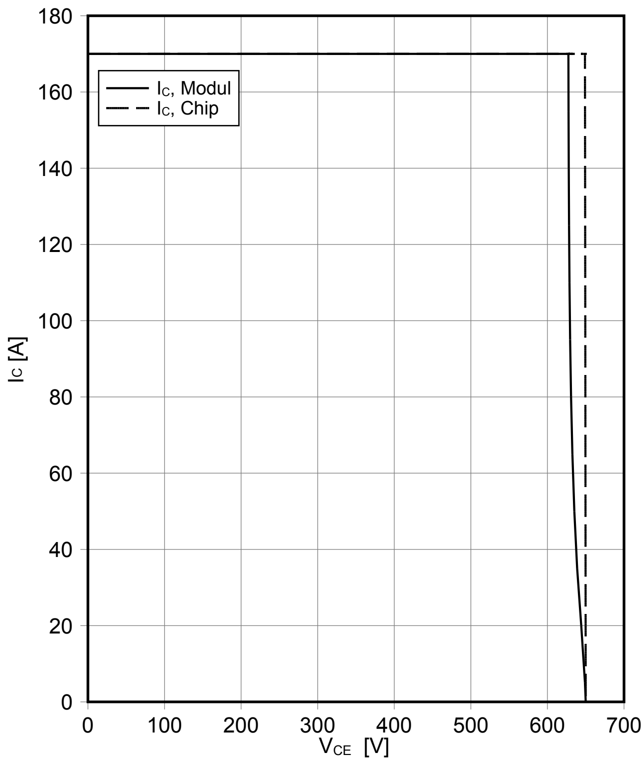
Schaltverluste IGBT, T2 / T3 (typisch)
switching losses IGBT, T2 / T3 (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
$V_{GE} = \pm15\ V$, $I_C = 85\ A$, $V_{CE} = 400\ V$



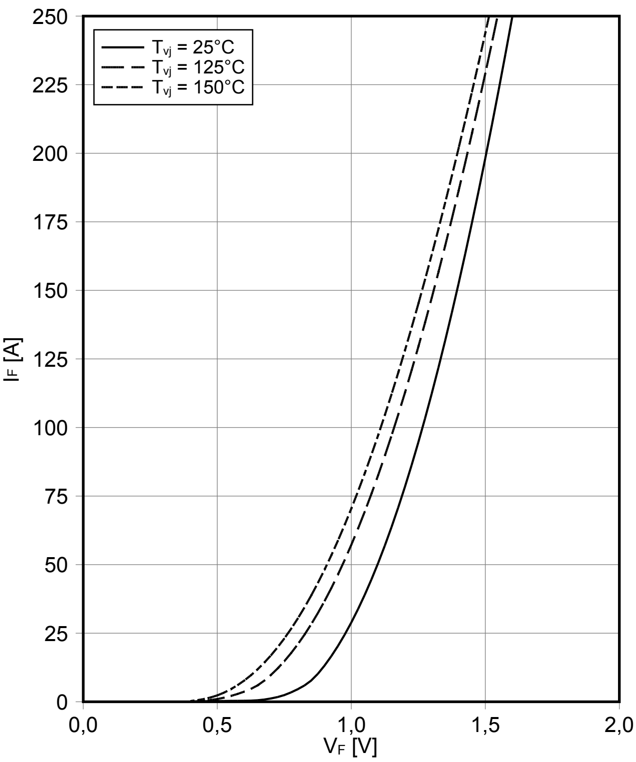
Transienter Wärmewiderstand IGBT, T2 / T3
transient thermal impedance IGBT, T2 / T3
Z_{thJH} = f (t)



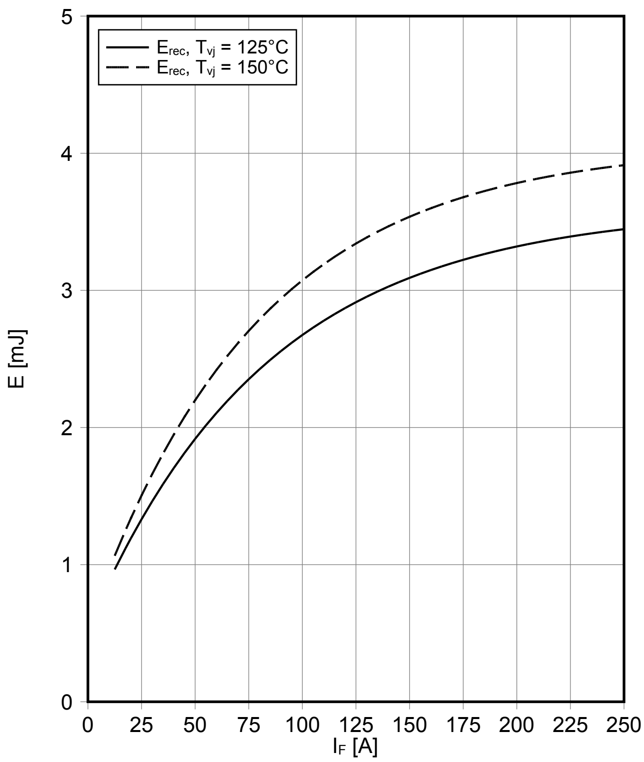
Sicherer Rückwärts-Arbeitsbereich IGBT, T2 / T3 (RBSOA)
reverse bias safe operating area IGBT, T2 / T3 (RBSOA)
I_C = f (V_{CE})
V_{GE} = ±15 V, R_{Goff} = 10 Ω, T_{vj} = 150°C



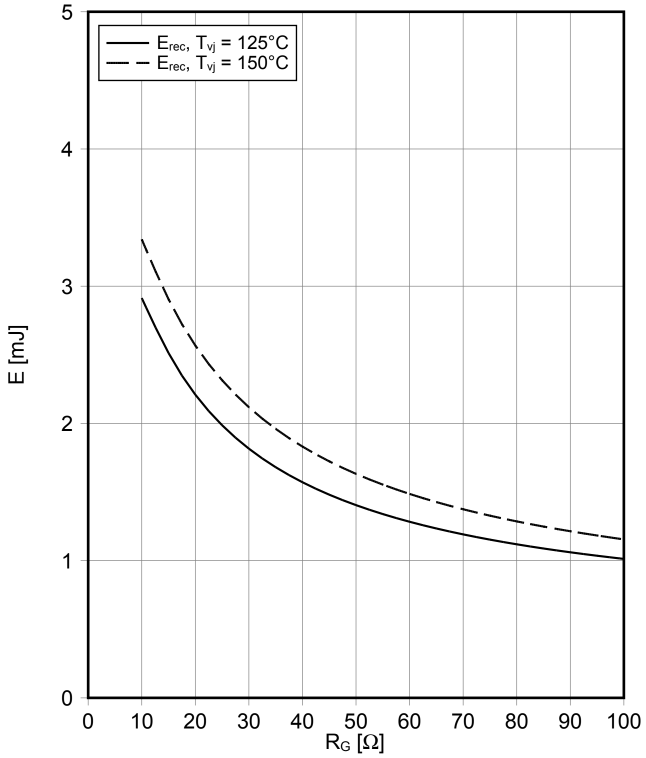
Durchlasskennlinie der Diode, D1 / D4 (typisch)
forward characteristic of Diode, D1 / D4 (typical)
I_F = f (V_F)



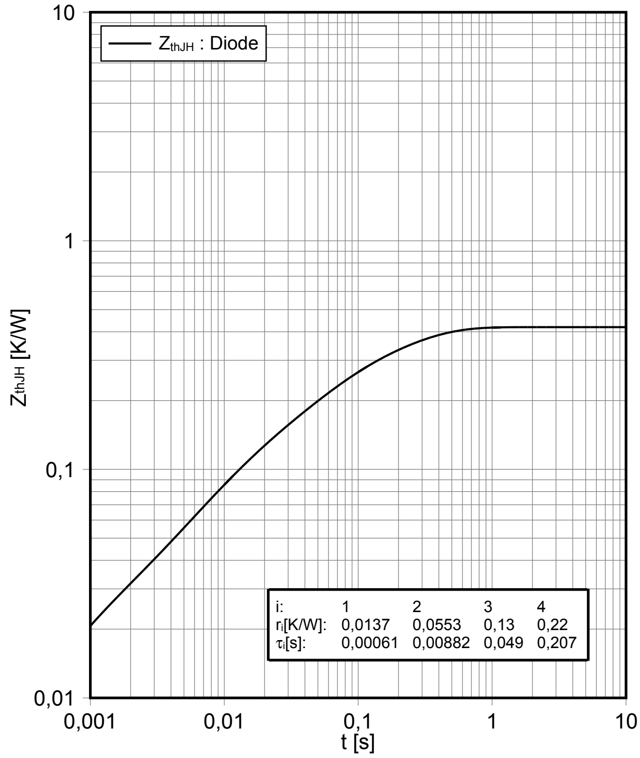
Schaltverluste Diode, D1 / D4 (typisch)
switching losses Diode, D1 / D4 (typical)
E_{rec} = f (I_F)
R_{Gon} = 10 Ω, V_{CE} = 400 V



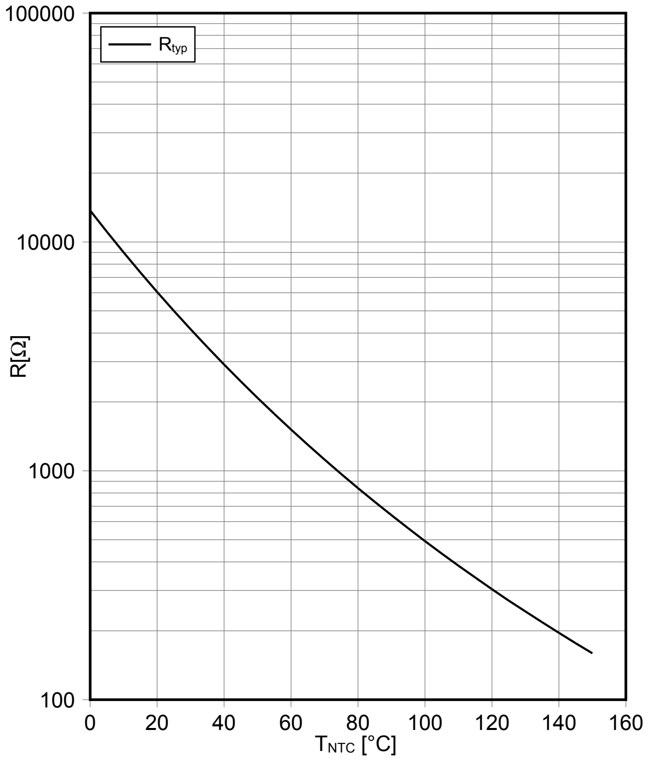
Schaltverluste Diode, D1 / D4 (typisch)
switching losses Diode, D1 / D4 (typical)
$E_{rec} = f(R_G)$
$I_F = 125$ A, $V_{CE} = 400$ V



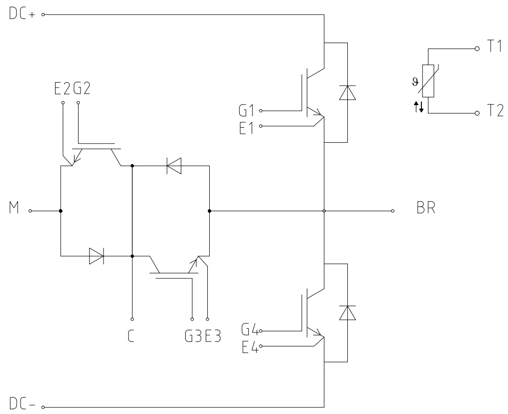
Transienter Wärmewiderstand Diode, D1 / D4
transient thermal impedance Diode, D1 / D4
$Z_{thJH} = f(t)$



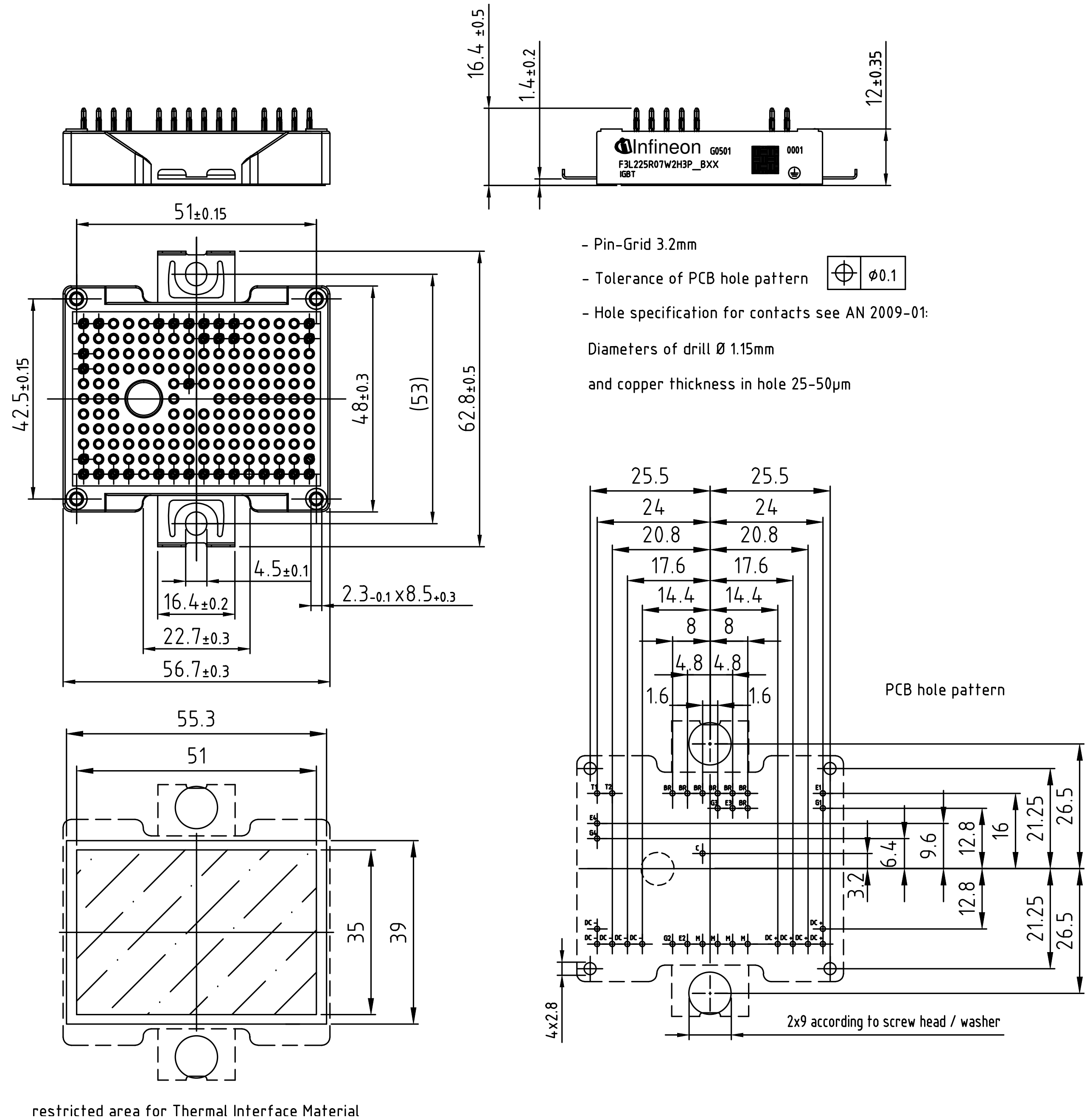
NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)
R = f (T)



Schaltplan / Circuit diagram



Gehäuseabmessungen / Package outlines



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Edition 2017-06-15

Published by
Infineon Technologies AG
81726 München, Germany

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Email: erratum@infineon.com